L Number	Hits	Search Text	DB	Time stamp
-	1	("6355515").PN.	USPAT	2003/09/08 02:50
-	1	"6204526".PN.	USPAT	2003/09/06 17:51
-	1	"6184075".PN.	USPAT	2003/09/06 17:51
-	1	"6143666".PN.	USPAT	2003/09/06 17:51
-	1	"6080655".PN.	USPAT	2003/09/06 17:51
-	1	"6043119".PN.	USPAT	2003/09/06 17:51
-	1	"6025277".PN.	USPAT	2003/09/06 17:51
-	1	"6008129".PN.	USPAT	2003/09/06 17:51
-	1	"5989623".PN.	USPAT	2003/09/06 17:51
-	1	"5920761".PN.	USPAT	2003/09/06 17:51
-	1	"5904576".PN.	USPAT	2003/09/06 17:51
-	1	"5851928".PN.	USPAT	2003/09/06 17:51
-	1	"5470790".PN.	USPAT	2003/09/06 17:51
-	1	"5225376".PN.	USPAT	2003/09/06 17:51
-	14	(("6355515").PN.) or "6204526".PN. or "6184075".PN. or "6143666".PN. or "6080655".PN. or "6043119".PN. or "6025277".PN. or "6008129".PN. or "5989623".PN. or "5920761".PN. or "5904576".PN. or "5851928".PN. or "5470790".PN. or "5225376".PN.	USPAT	2003/09/06 18:07
-	0	("sramand(conduct$3)and(insulatorordielectri")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:25
-	0	("sramand(conduct$3)and(insulatorordielectri")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/06 18:09
-	3006	sram and(conduct$3)and(insulator or dielectric)	USPAT	2004/02/17 12:59
-	2949	(sram and(conduct$3)and(insulator or dielectric)) and (tungsten or aluminum or al or ta)	USPAT	2003/09/08 03:25
-	824	((sram and(conduct$3)and(insulator or dielectric)) and (tungsten or aluminum or al or ta)) and (sio or siliconoxide or (silicon near2 oxide)) and (siliconnitride or sin or (silicon near2 nitride))	USPAT	2003/09/06 19:26
-	1	("5780910").PN.	USPAT	2003/09/06 19:45
-	984	(etch adj rate) and bpsg	USPAT	2003/09/06 19:46
-	96	(etch adj rate) near5 bpsg	USPAT	2003/09/06 20:35
-	35	((etch adj rate) near5 bpsg) and ((silicon adj oxide) or sio or siliconoxide)	USPAT	2003/09/06 19:47
-	21	((etch adj rate) near5 bpsg) and (bpsg SAME ((silicon adj oxide) or sio or siliconoxide))	USPAT	2003/09/06 19:51
-	2	((etch adj rate) near5 bpsg) and usg	USPAT	2003/09/06 20:50
-	1	("5754467").PN.	USPAT	2003/09/06 20:50
-	1	("6025277").PN.	USPAT	2003/09/08 03:25
-	578	257/211.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	635	257/202.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:25
-	446	257/741.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:26

-	148	257/748.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:26
-	2367	257/758.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:26
-	1187	257/763.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/09/08 03:26
-	600	257/211.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	656	257/202.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	455	257/741.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	158	257/748.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	2573	257/758.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	1220	257/763.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 12:33
-	5562	sram and(conduct$3 or metal)and(insulator or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 13:01
-	167939	257/$6.ccls.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 13:00
-	2261	257/$6.ccls. and sram and(conduct$3 or metal)and(insulator or dielectric)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 13:01
-	1	("6355515").PN.	USPAT	2004/02/17 13:15
-	1	"6204526".PN.	USPAT	2004/02/17 13:21
-	1	"6184075".PN.	USPAT	2004/02/17 13:21
-	1	"6143666".PN.	USPAT	2004/02/17 13:22
-	1	"6080655".PN.	USPAT	2004/02/17 13:22
-	1	"6080655".PN.	USPAT	2004/02/17 13:22
-	1	"6080655".PN.	USPAT	2004/02/17 13:23
-	1	"6025277".PN.	USPAT	2004/02/17 13:23
-	1	"6008129".PN.	USPAT	2004/02/17 13:34
-	1	"5989623".PN.	USPAT	2004/02/17 13:34
-	1	"5920761".PN.	USPAT	2004/02/17 13:34
-	1	"5904576".PN.	USPAT	2004/02/17 13:34

-	1	"5851928".PN.	USPAT	2004/02/17 13:34
-	1	"5470790".PN.	USPAT	2004/02/17 13:34
-	1643	257/$6.ccls. and (sram and(conduct$3 or metal)and(insulator or dielectric))	USPAT; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 21:09
-	2261	257/$6.ccls. and (sram and(conduct$3 or metal)and(insulator or dielectric))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 21:09
-	618	(257/$6.ccls. and (sram and(conduct$3 or metal)and(insulator or dielectric))) not (257/$6.ccls. and (sram and(conduct$3 or metal)and(insulator or dielectric)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/02/17 21:09